

LISTING of CLAIMS

1-12. (Cancelled)

13. (Currently amended) A process for selectively removing silicon dioxide and photoresist sidewall residue after dry etching of a semiconductor wafer comprising treating the wafer after dry etching with a solution consisting essentially of;

- (a) sulfuric acid,
- (b) hydrogen fluoride, ammonium fluoride or an alkali metal fluoride,
- and
- (c) hydrogen peroxide,
- and
- (d) water,

wherein said solution contacts said sidewall residue effectively to remove it from said dry etched wafer,

and wherein the ratio (a):(b) is in the range of from 10:1 to 700:1 by weight.

- 14. (Previously presented) A process for removing photoresist according to claim 13, wherein the photoresist is effective for g-line, i-line, deep UV, E-beam or X-ray.
- 15. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated at a temperature of from 0 to 140 degrees C.
- 16. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated for about 10 minutes.
- 17. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the operation pressure is maintained at about 1 atm.
- 18. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the etch rate of the wafer is less than 1 Å/min.

19. (Previously presented) A process for removing photoresist after dry etching according to claim 15, wherein the wafer is treated at a temperature of from 120 to 140 degrees C.
20. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein (b) is hydrogen fluoride.
21. (Previously presented) A process for selectively removing silicon dioxide and photoresist after dry etching of a semiconductor wafer comprising treating the wafer after dry etching with a solution consisting essentially of sulfuric acid, hydrofluoric acid and hydrogen peroxide wherein the ratio of sulfuric acid plus hydrofluoric acid to hydrogen peroxide is 3:1 by volume.
22. (Cancel)
23. (Cancel)
24. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the ratio (a):(b) is in the range of from 100:1 to 700:1 by weight.
25. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the ratio (a):(b) is in the range of from 300:1 to 500:1 by weight.
26. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the ratio of sulfuric acid plus ammonium fluoride to hydrogen peroxide is 3:1 by volume.
27. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein (b) is ammonium fluoride or an alkali metal fluoride.